



April 2014

# FQA11N90C\_F109

## N-Channel QFET<sup>®</sup> MOSFET

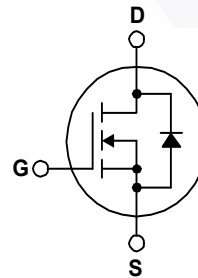
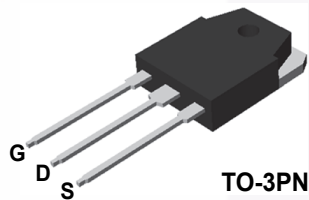
900 V, 11.0 A, 1.1  $\Omega$

### Features

- 11 A, 900 V,  $R_{DS(on)} = 1.1 \Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 5.5 \text{ A}$
- Low Gate Charge (Typ. 60 nC)
- Low Crss (Typ. 23 pF)
- 100% Avalanche Tested
- RoHS compliant

### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol         | Parameter   | FQA11N90C_F109                             | Unit                |
|----------------|---|--|---------------------|
| $V_{DSS}$      | Drain to Source Voltage   | 900  | V                   |
| $I_D$          | Drain Current   | - Continuous ( $T_C = 25^\circ\text{C}$ )  | 11.0                |
|                |   | - Continuous ( $T_C = 100^\circ\text{C}$ ) | 6.9                 |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)   | 44.0                                       | A                   |
| $V_{GSS}$      | Gate to Source Voltage  | $\pm 30$                                   | V                   |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)   | 960  | mJ                  |
| $I_{AR}$       | Avalanche Current (Note 1)  | 11.0                                       | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)  | 30   | mJ                  |
| dv/dt          | Peak Diode Recovery dv/dt (Note 3)  | 4.0  | V/ns                |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )<br>- Derate Above $25^\circ\text{C}$ | 300  | W                   |
|                |   | 2.38                                       | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range   | -55 to +150                                | $^\circ\text{C}$    |
| $T_L$          | Maximum Lead Temperature for Soldering,<br>1/8" from Case for 5 Seconds             | 300  | $^\circ\text{C}$    |

### Thermal Characteristics

| Symbol          | Parameter                                    | FQA11N90C_F109 | Unit                      |
|-----------------|--|----------------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max    | 0.42           | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max | 40             | $^\circ\text{C}/\text{W}$ |

FQA11N90C\_F109 — N-Channel QFET<sup>®</sup> MOSFET

## Package Marking and Ordering Information

| Part Number    | Top Mark  | Package | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|-----------|---------|----------------|-----------|------------|----------|
| FQA11N90C_F109 | FQA11N90C | TO-3PN  | Tube           | N/A       | N/A        | 30 units |

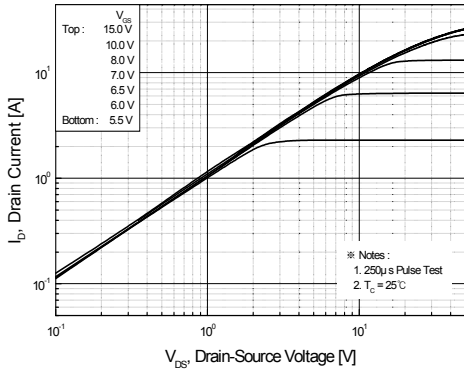
## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

| Symbol  | Parameter   | Test Conditions   | Min      | Typ  | Max  | Unit                      |
|---|---|---|----------|------|------|---------------------------|
| <b>Off Characteristics</b>                                    |   |   |          |      |      |                           |
| $BV_{DSS}$  | Drain-Source Breakdown Voltage                        | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$                           | 900      | --   | --   | V                         |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$                          | Breakdown Voltage Temperature Coefficient             | $I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$             | --       | 1.02 | --   | $\text{V}/^\circ\text{C}$ |
| $I_{DSS}$   | Zero Gate Voltage Drain Current                       | $V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$                            | --       | --   | 10   | $\mu\text{A}$             |
|   |   | $V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$                        | --       | --   | 100  | $\mu\text{A}$             |
| $I_{GSSF}$  | Gate-Body Leakage Current, Forward                    | $V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$                             | --       | --   | 100  | nA                        |
| $I_{GSSR}$  | Gate-Body Leakage Current, Reverse                    | $V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$                            | --       | --   | -100 | nA                        |
| <b>On Characteristics</b>                                     |   |   |          |      |      |                           |
| $V_{GS(th)}$  | Gate Threshold Voltage                                | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$                               | 3.0      | --   | 5.0  | V                         |
| $R_{DS(on)}$  | Static Drain-Source On-Resistance                     | $V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$                              | --       | 0.91 | 1.1  | $\Omega$                  |
| $g_{FS}$  | Forward Transconductance                              | $V_{DS} = 50\text{ V}, I_D = 5.5\text{ A}$                              | --       | 9.0  | --   | S                         |
| <b>Dynamic Characteristics</b>                                |   |   |          |      |      |                           |
| $C_{iss}$   | Input Capacitance                                     | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$    | --       | 2530 | 3290 | pF                        |
| $C_{oss}$   | Output Capacitance                                    |   | --       | 215  | 280  | pF                        |
| $C_{rss}$   | Reverse Transfer Capacitance                          |   | --       | 23   | 30   | pF                        |
| <b>Switching Characteristics</b>                              |   |   |          |      |      |                           |
| $t_{d(on)}$   | Turn-On Delay Time                                    | $V_{DD} = 450\text{ V}, I_D = 11.0\text{ A},$<br>$R_G = 25\ \Omega$     | --       | 60   | 130  | ns                        |
| $t_r$   | Turn-On Rise Time                                     |   | --       | 130  | 270  | ns                        |
| $t_{d(off)}$  | Turn-Off Delay Time                                   |   | --       | 130  | 270  | ns                        |
| $t_f$   | Turn-Off Fall Time                                    |   | (Note 4) | --   | 85   | 180                       |
| $Q_g$   | Total Gate Charge                                     | $V_{DS} = 720\text{ V}, I_D = 11.0\text{ A},$<br>$V_{GS} = 10\text{ V}$ | --       | 60   | 80   | nC                        |
| $Q_{gs}$  | Gate-Source Charge                                    |   | --       | 13   | --   | nC                        |
| $Q_{gd}$  | Gate-Drain Charge                                     |   | (Note 4) | --   | 25   | --                        |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |   |   |          |      |      |                           |
| $I_S$   | Maximum Continuous Drain-Source Diode Forward Current |   | --       | --   | 11.0 | A                         |
| $I_{SM}$  | Maximum Pulsed Drain-Source Diode Forward Current     |   | --       | --   | 44.0 | A                         |
| $V_{SD}$  | Drain-Source Diode Forward Voltage                    | $V_{GS} = 0\text{ V}, I_S = 11.0\text{ A}$                              | --       | --   | 1.4  | V                         |
| $t_{rr}$  | Reverse Recovery Time                                 | $V_{GS} = 0\text{ V}, I_S = 11.0\text{ A},$                             | --       | 1000 | --   | ns                        |
| $Q_{rr}$  | Reverse Recovery Charge                               | $di_F / dt = 100\text{ A}/\mu\text{s}$                                  | --       | 17.0 | --   | $\mu\text{C}$             |

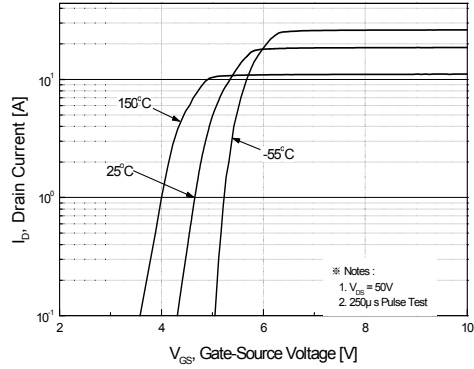
### Notes :

1. Repetitive rating : pulse width limited by maximum junction temperature.
2.  $L = 15\text{ mH}, I_{AS} = 11.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 11.0\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

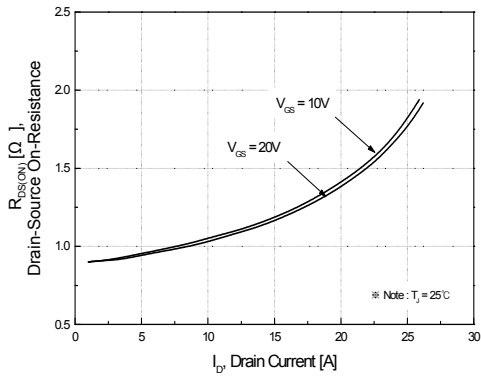
## Typical Characteristics



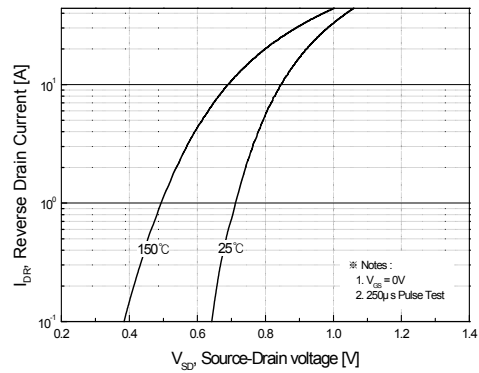
**Figure 1. On-Region Characteristics**



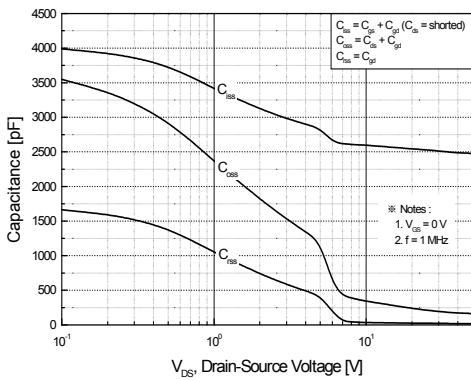
**Figure 2. Transfer Characteristics**



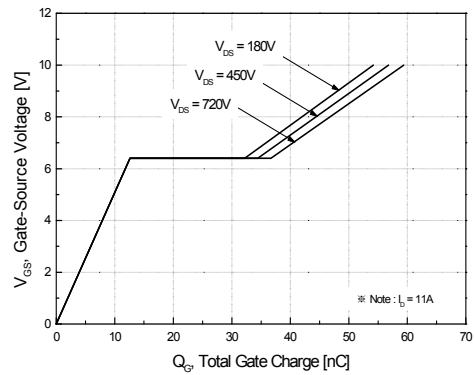
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**

## Typical Characteristics (Continued)

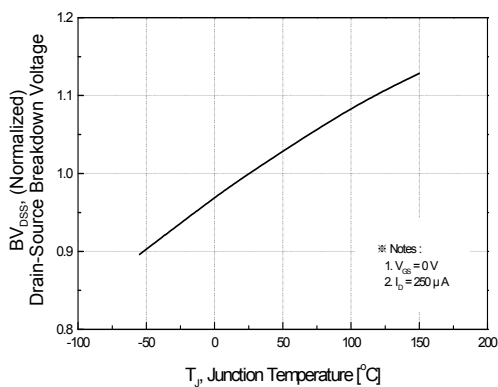


Figure 7. Breakdown Voltage Variation

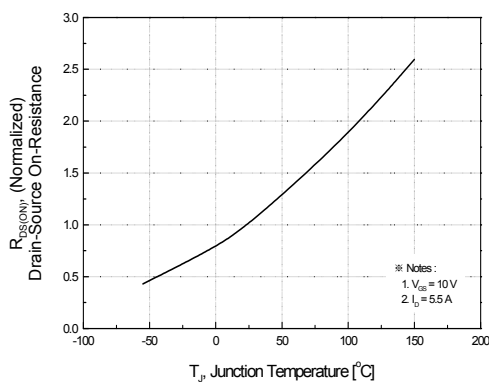


Figure 8. On-Resistance Variation

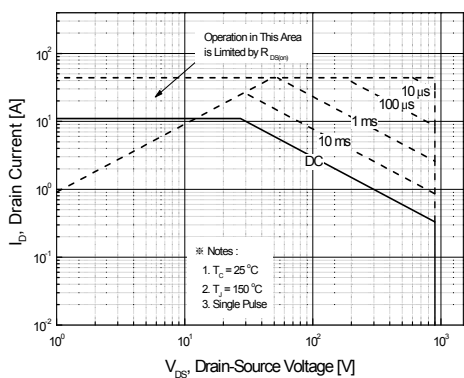


Figure 9. Maximum Safe Operating Area

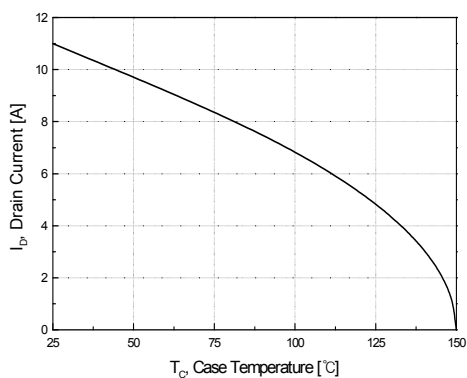


Figure 10. Maximum Drain Current vs Case Temperature

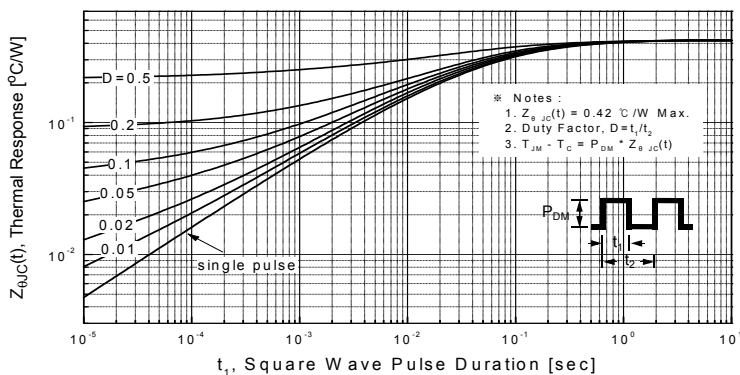
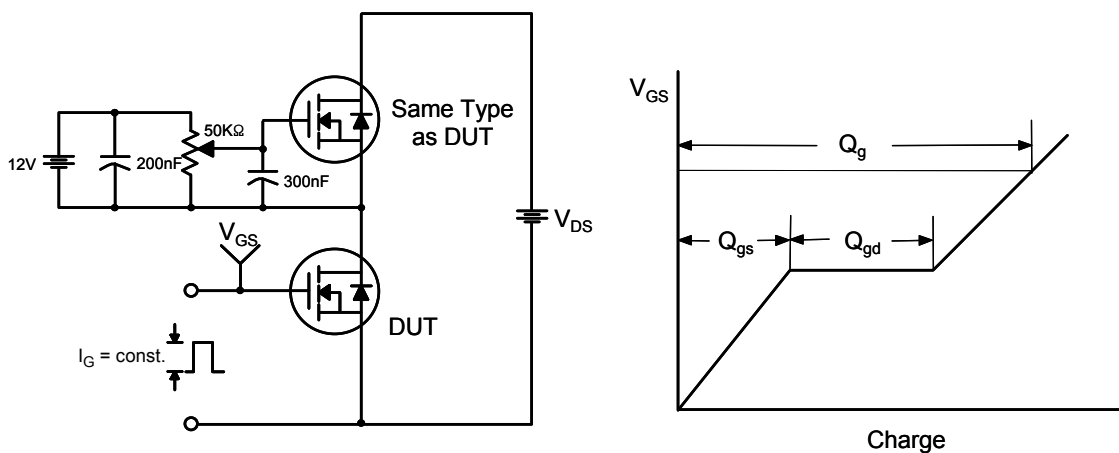
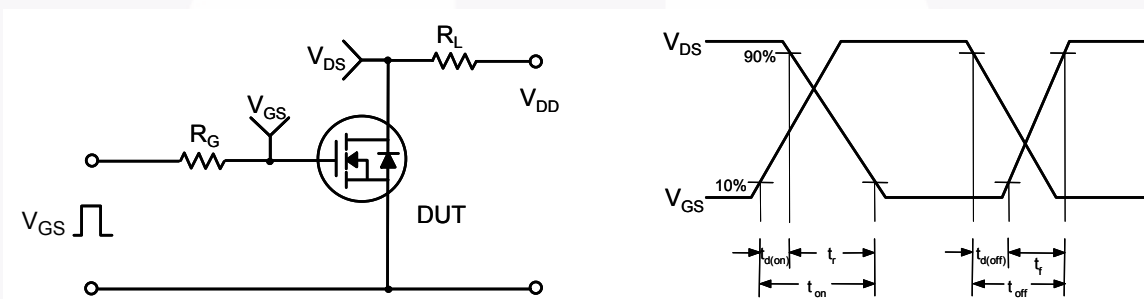


Figure 11. Transient Thermal Response Curve

**Figure 12. Gate Charge Test Circuit & Waveform**



**Figure 13. Resistive Switching Test Circuit & Waveforms**



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

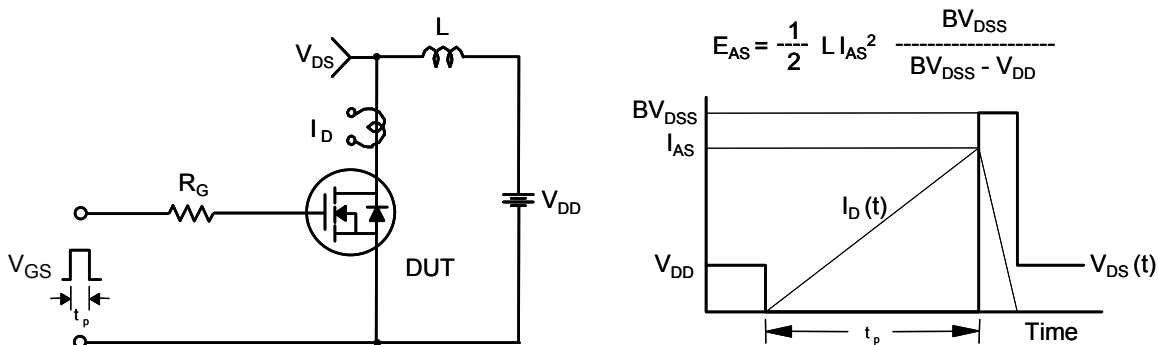
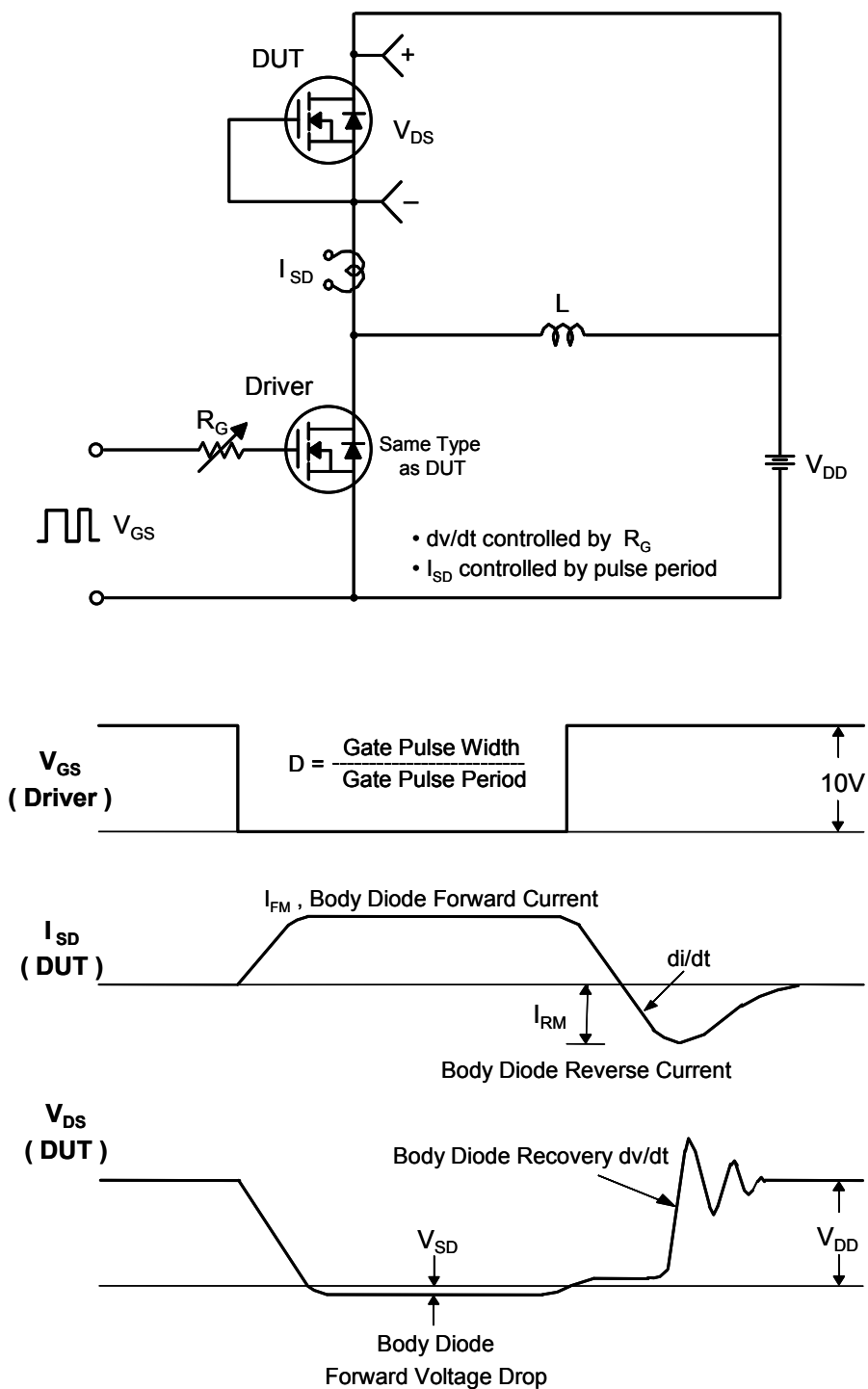
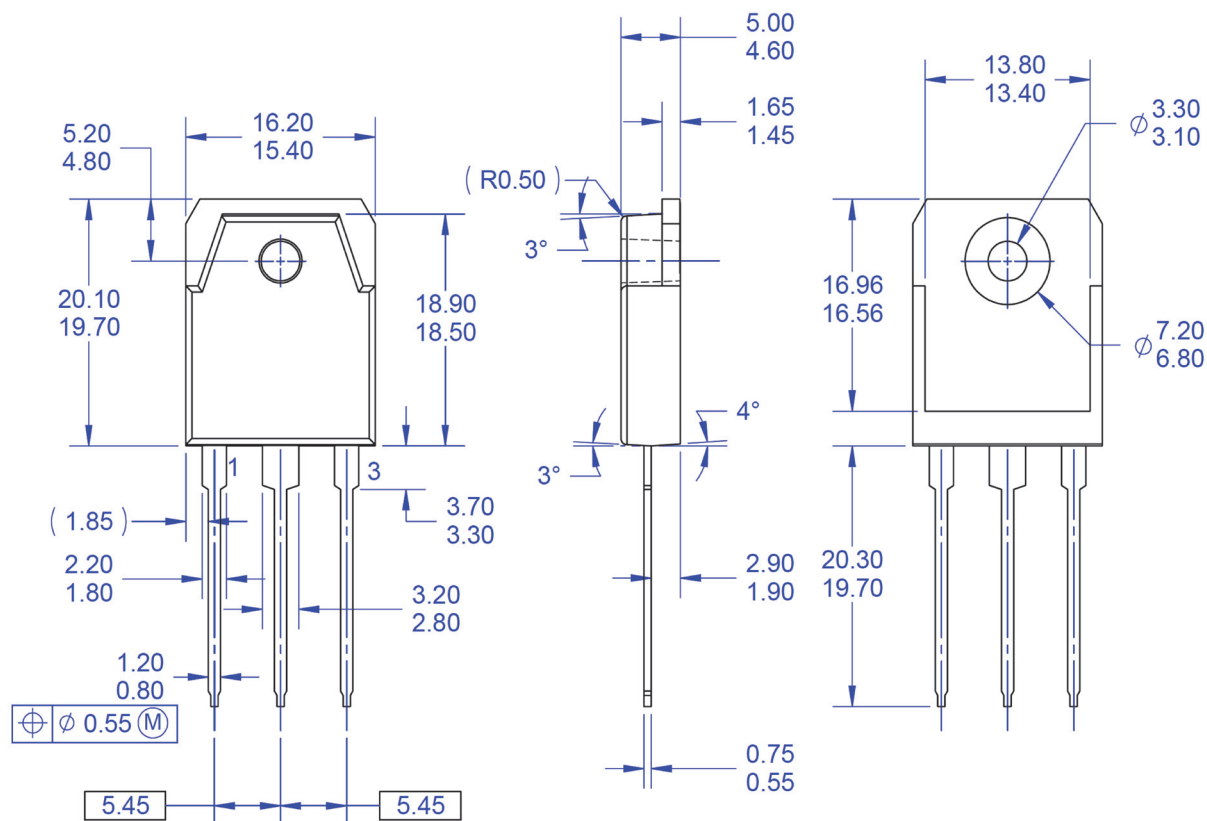


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

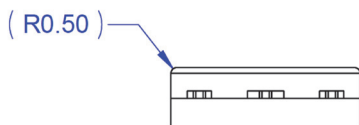


## Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- E) DRAWING FILE NAME: TO3PN03AREV1.
- F) FAIRCHILD SEMICONDUCTOR.



**Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65**

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